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advanced process control systems and solutions

Imperia™

Advanced Process Control for Compound Semiconductor and HB-LED

Nanometrics Incorporated
[Corporate Headquarters]
1550 Buckeye Drive
Milpitas, CA 95035 USA
tel 408.545.6000

Materials Characterization Group
1320 SE Armour Road
Suite B-2
Bend, OR 97702 USA
tel 541.322.2500

www.nanometrics.com

Nanometrics Japan
1F, Pola Dai3 Gotanda Building
8-9-5 Nishi-Gotanda
Shinagawa-ku, Tokyo 141-0031
JAPAN
tel +81 3 5745 9305

Nanometrics Korea
3rd Floor
Hwasung Post Office Building 59-2
Sukwoo-dong Hwasung City Gyeonggi-do
SOUTH KOREA 445-170
tel +82 31 231 8600

China | Taiwan Regions

Quatek Inc.
Unit 2112, 21F, Yong Sheng Tower 2025
West Zhong Shan Road
Shanghai 200235 **CHINA (PRC)**
tel +86 21 64813366

Quatek Co., Ltd.
[Corporate Headquarters]
4/F.,308,Sec.1 Nei Hu Road
Nei Hu, Taipei 11493 **TAIWAN (ROC)**
tel +886 2 27973357
www.quatek.com.tw

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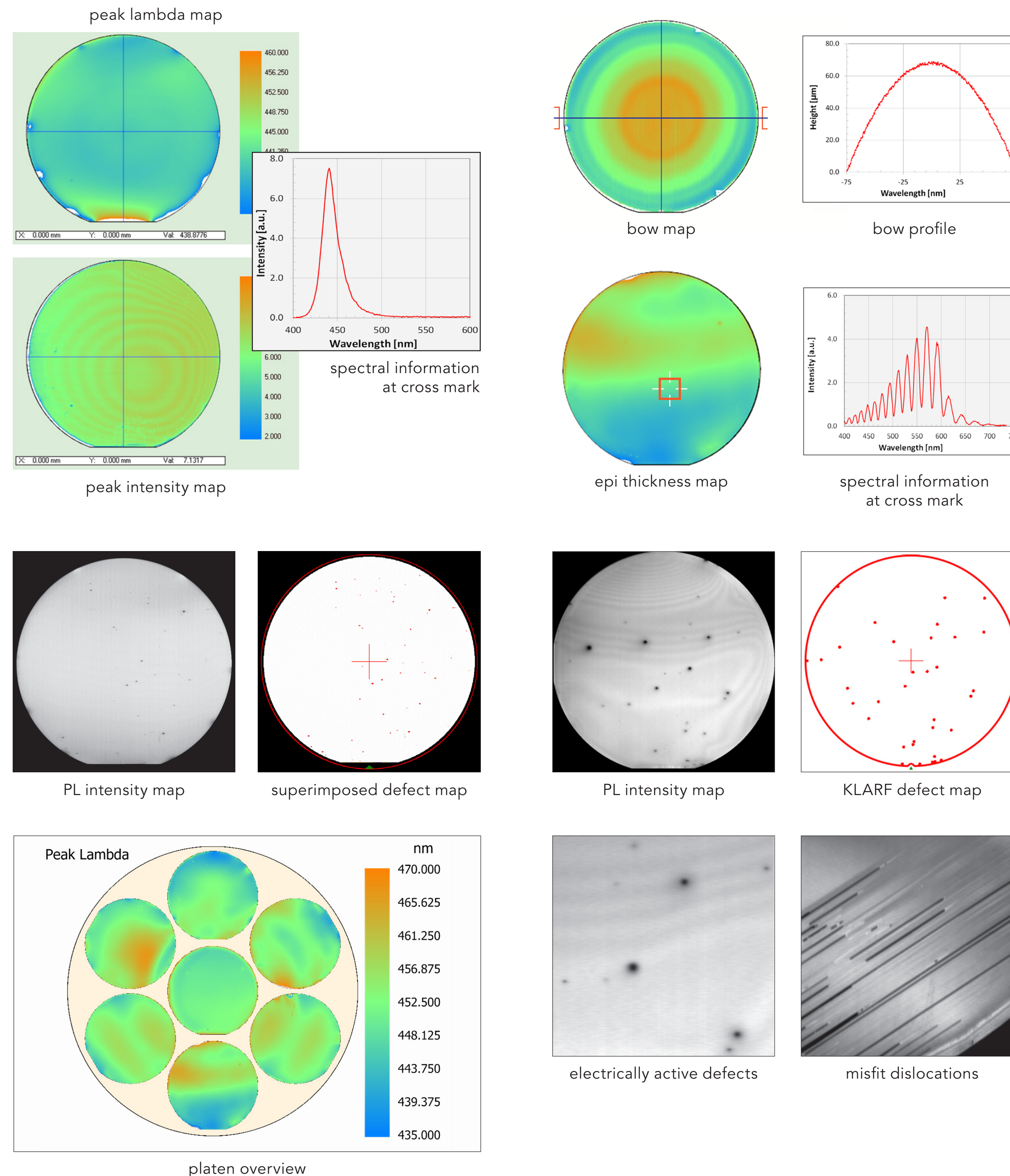
With its unique optical design technology, the Imperia detects and classifies yield-killing defects with the additional benefit of simultaneous state-of-the-art photoluminescence (PL) production monitoring.

There are significant economic savings to be gained by more accurately predicting MOCVD reactor yield and PM schedules. Combining these two post-epitaxial metrology screening functions into a single high throughput system minimizes valuable fab space use and cassette handling time.

- Simultaneous photoluminescence measurement with defect inspection
- Defect analysis and classification software capabilities
- High throughput for large substrates, 90 WPH for 150 mm samples
- Fully automated platform with GEM/SECS II capabilities
- Illumination wavelength options at 532, 405, 375 and 355 nm
- Detection options at 350-850 nm and 400-1,000 nm



Photoluminescence Mapping

High density imaging of peak lambda, peak intensity, FWHM and other LED materials relevant parameters

Measurement accuracy and reproducibility (≤1 nm)

Capability of measuring bare and patterned wafers at resolutions down to 125 µm

Defect Inspection and Analysis

High resolution mapping for defect inspection down to 125 µm

Brightfield PL channel for detecting electrically active defects

Defect extraction, morphological analysis and quantification

Die-based yield binning capabilities allow yield prediction on a die level

Real-Time Defect Extractor (RDE) software with KLARF output

Epitaxial Layer Thickness

Epitaxial layer thickness and normalized reflectivity imaging at high resolution down to 125 µm

Excellent measurement accuracy (2% of nominal thickness) and reproducibility (1δ ≤ 1%)

Wafer Bow

Wafer shape profiling at multiple angles and high resolution down to 125 µm

Full wafer 3D bow reconstruction via data interpolation and smoothing

±500 µm bow measurement range and ±6 µm reproducibility